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A Self Learning Algorithm for NAND Flash Controllers

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Outline

- Basic FW Architecture
- Challenges & Problems
- Self-learning & Adaptive Algorithm
- Conclusion

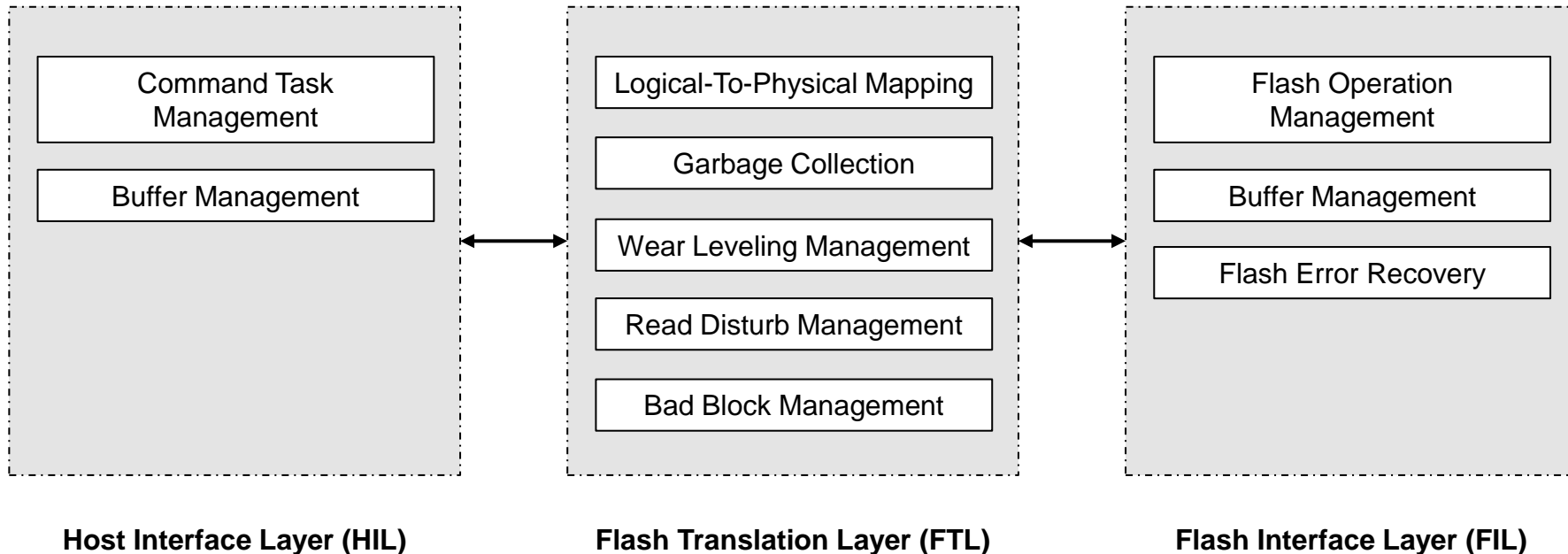


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Basic FW Architecture



Brief Overview





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Challenges & Problems



Performance

- Read/Write Latency
 - Different hosts have different I/O patterns
 - Inefficient host latency management results in unstable performance
- Idle Time Operations
 - Controller performs background operations or enters power saving mode during system idle
 - Redundant operations will not only consume more power, but also impact WAF and latency time of next command



Endurance

- Data Integrity
 - Sudden power loss, data retention and read disturbance will lead to data corruption in NAND flash
- Device Lifetime
 - NAND flash has limited P/E cycle
 - Unbalance SLC/TLC block usage will induce higher WAF and cause NAND flash to wear out quickly



Cost

- Over Provision
 - WAF can be greatly reduced by allocating more spare blocks
 - However, higher OP means lesser logical space for user



Flexibility

- Firmware Update
 - Different host platforms have dissimilar IO patterns
 - Several FW versions optimized to serve each platform can be costly to maintain



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Self Learning & Adaptive Algorithm



Objective

- FW with configurable parameters is simply not enough
- The following to be considered
 - a. Data/pattern aware
 - b. Self adaptive
 - c. Self learning



Key Parameters

HOST

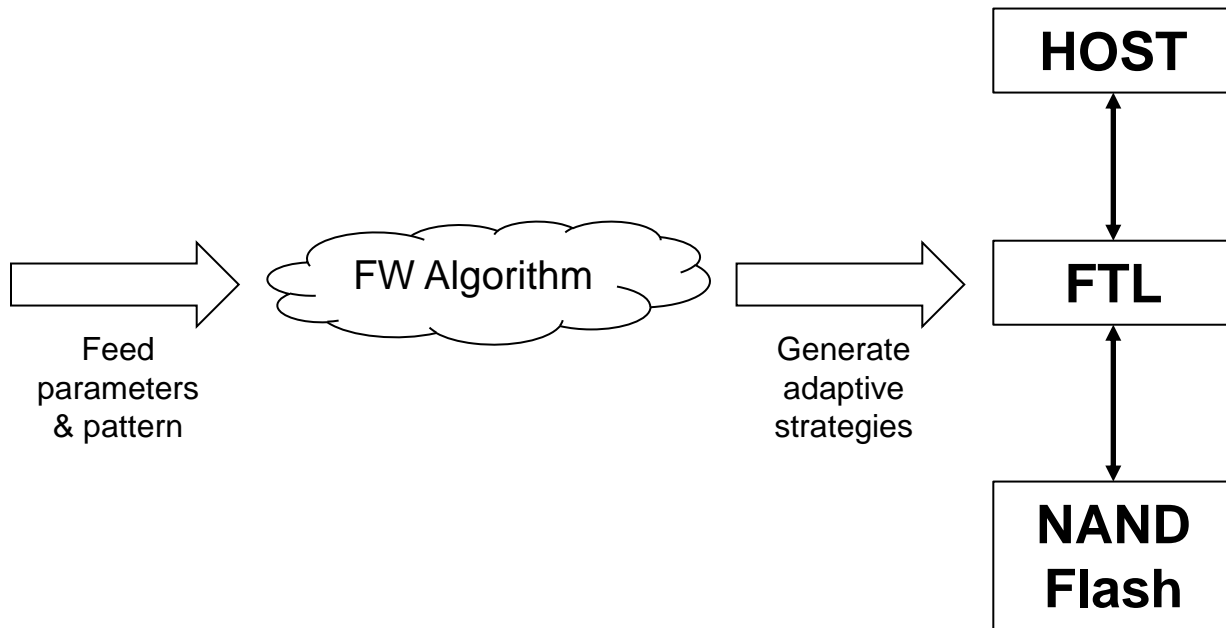
1. Read/Write IO Pattern
2. System Idle Behavior

FTL

1. Block Usage
2. Block Density
3. Block Age
4. Table Hit Pattern

NAND FLASH

1. Erase Count
2. Read Count
3. Flash Error Condition

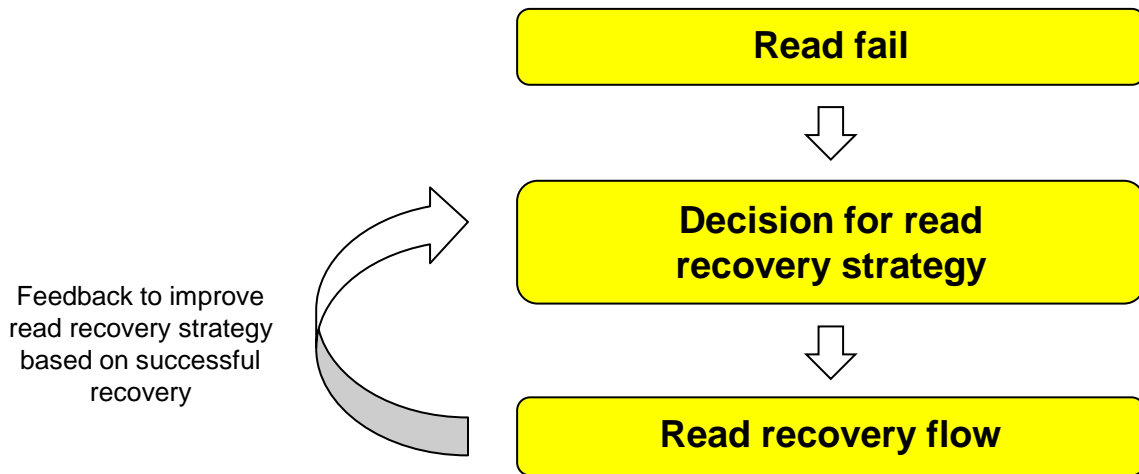




Dynamic Read Recovery Strategy

- Due to the reliability issues of 3D NAND, the read recovery flow has been more sophisticated and time consuming than before
- Such as, the expansion of read retry tables in NAND flash
- The device performance can be severely impacted especially during end of life

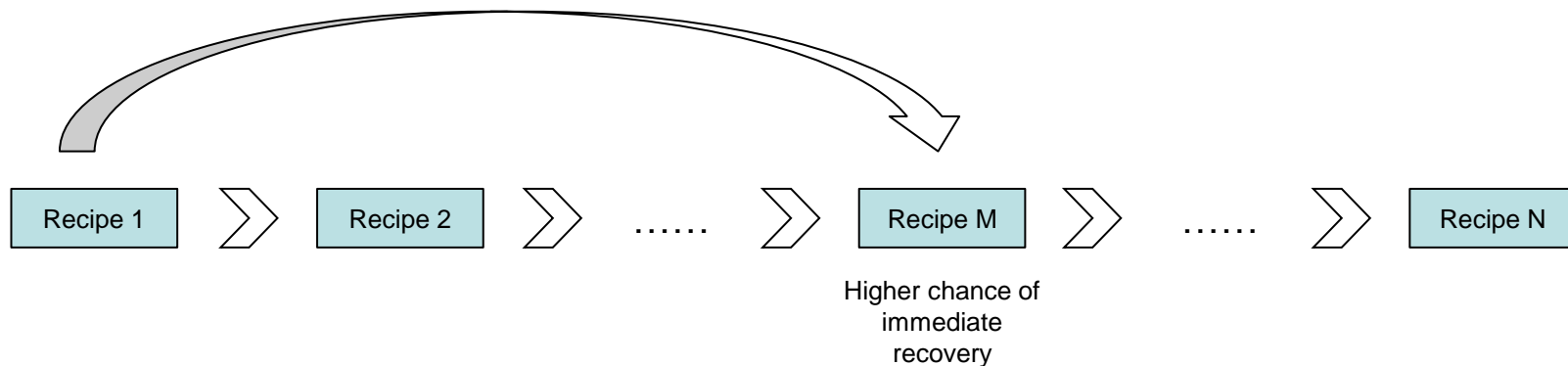
Dynamic Read Recovery Strategy



- Controller can monitor the status of NAND flash and learn from previous recovery statistics to optimize the recovery flow

Dynamic Read Recovery Strategy

Adaptive recovery strategy can rearrange the priority of recovery flow



- Controller will eventually learn along the iterative process and determine the best approach

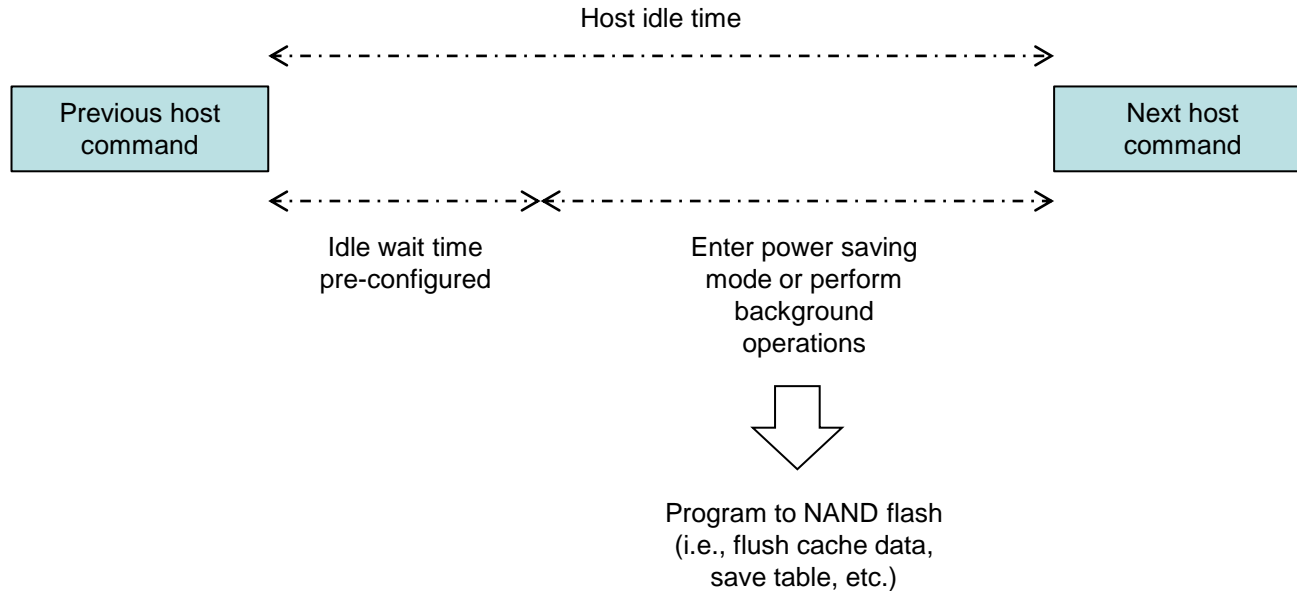


Idle Time Optimization

- Controller usually waits for a period of idle time (pre-configured by user) and then performs background operations or enters power saving mode
- During these operations, some data will be programmed into NAND flash



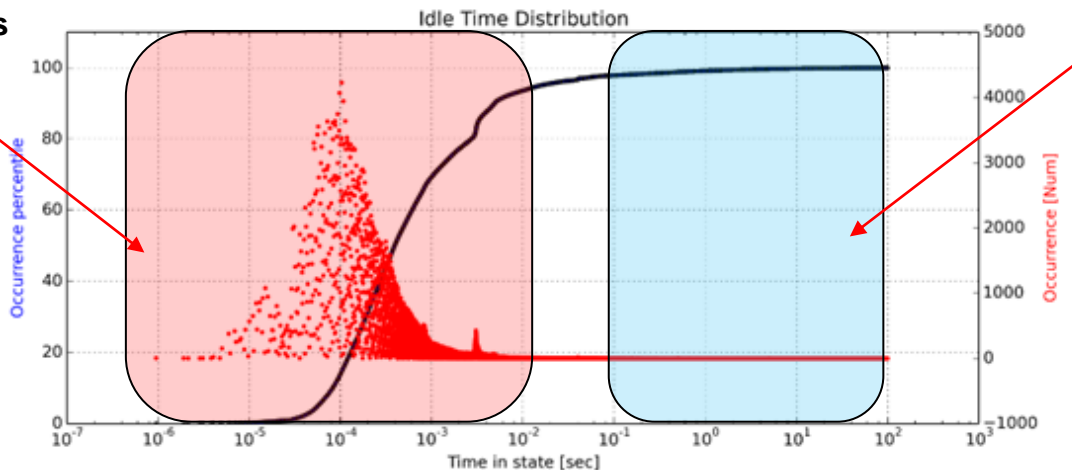
Idle Time Optimization





Idle Time Optimization

Most of the idle time is lower than 10ms

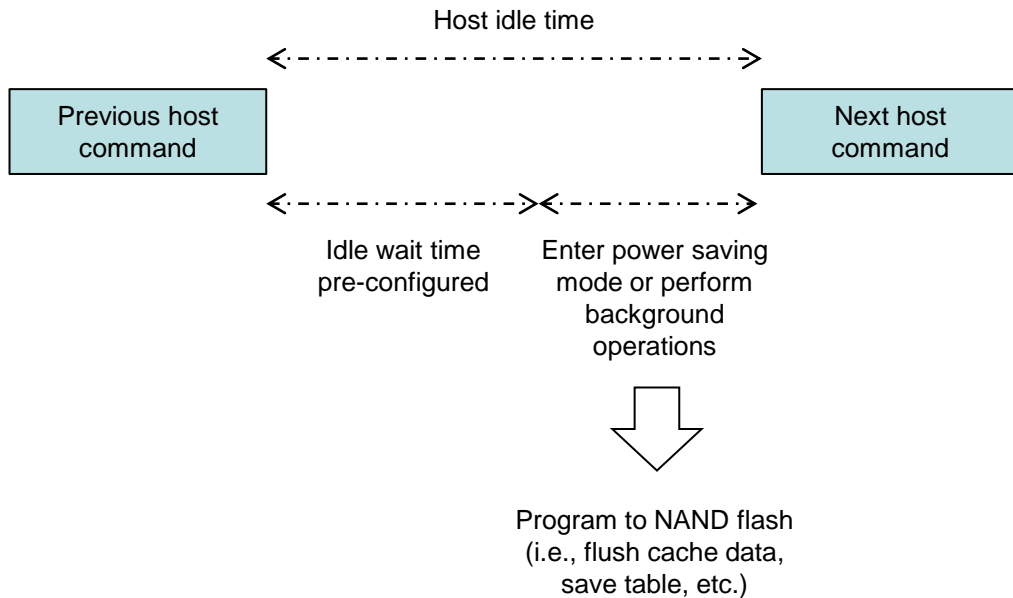


Main contribution of the idle time is more than 100ms

- However, different hosts may have different idle time behavior



Idle Time Optimization

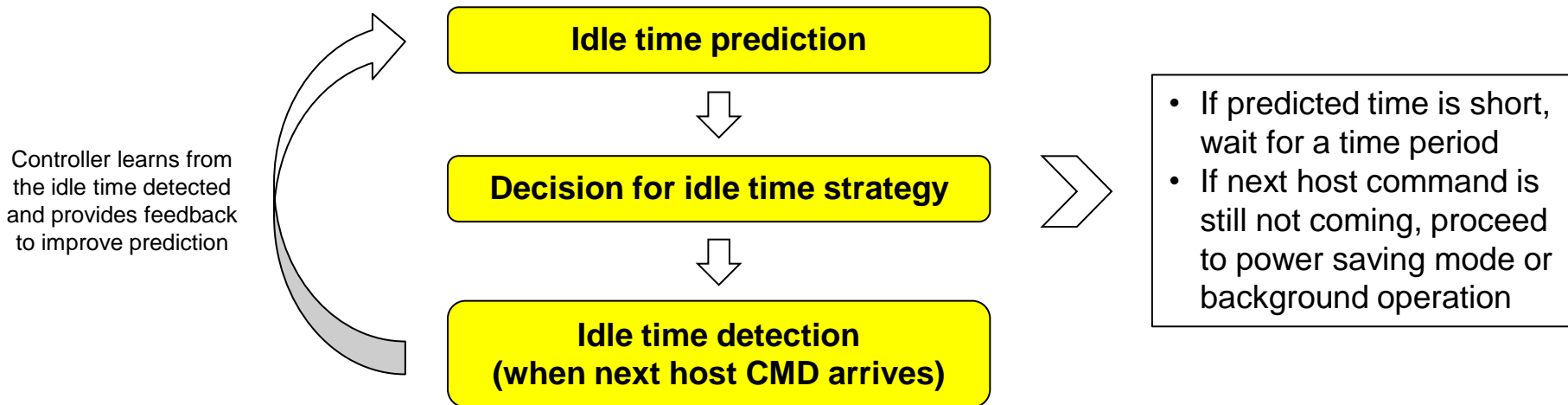


- Redundant NAND flash program operations will increase erase count



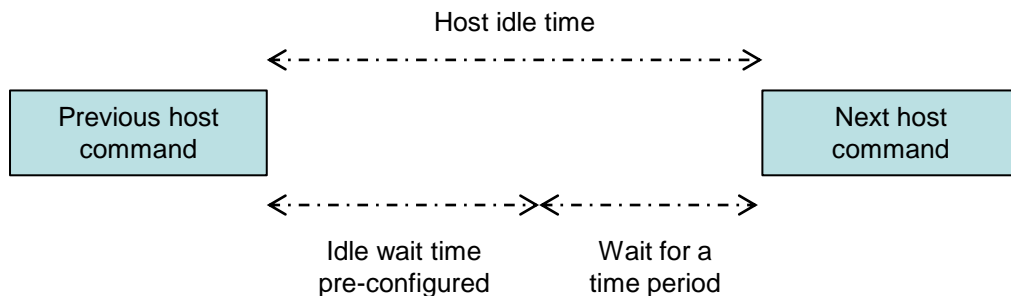
Idle Time Optimization

- What if the controller can learn from the host behavior and predict for an optimized strategy?





Idle Time Optimization

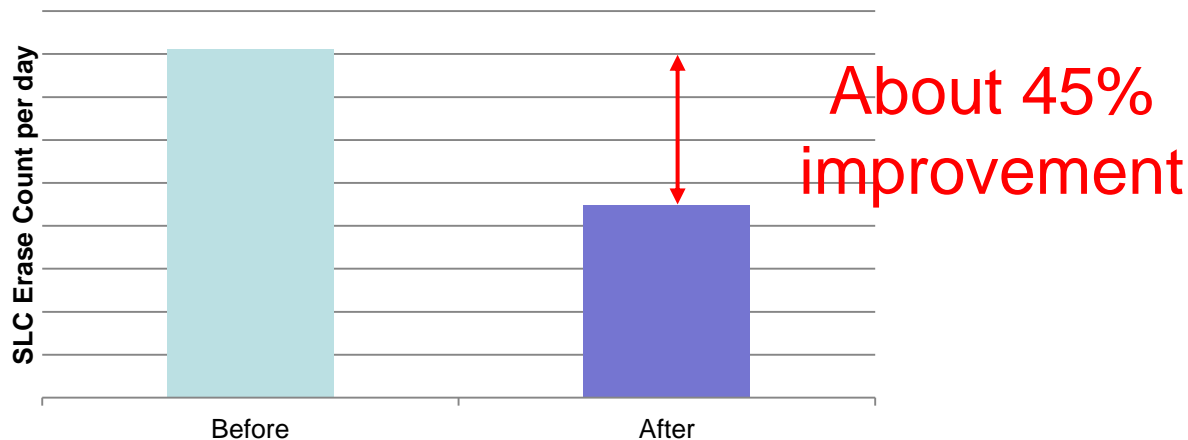


- An adaptive idle time strategy can greatly reduce redundant programs to NAND flash



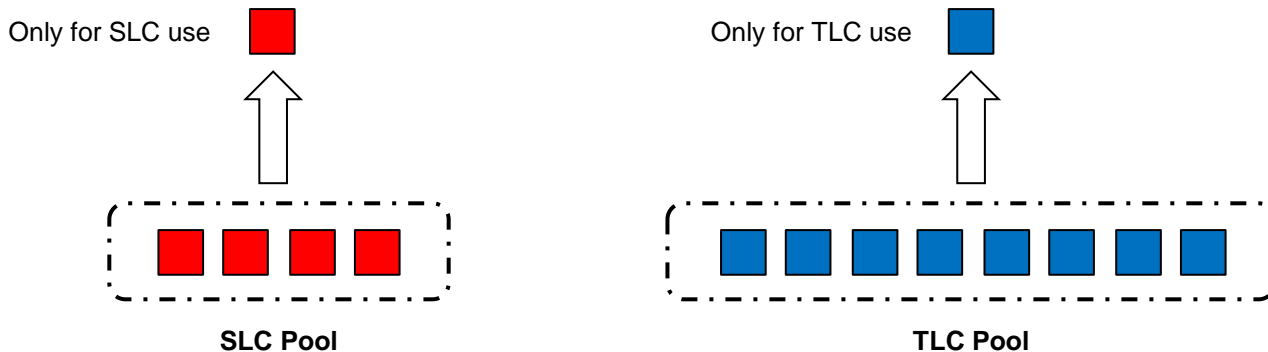
Idle Time Optimization

Simulation Results



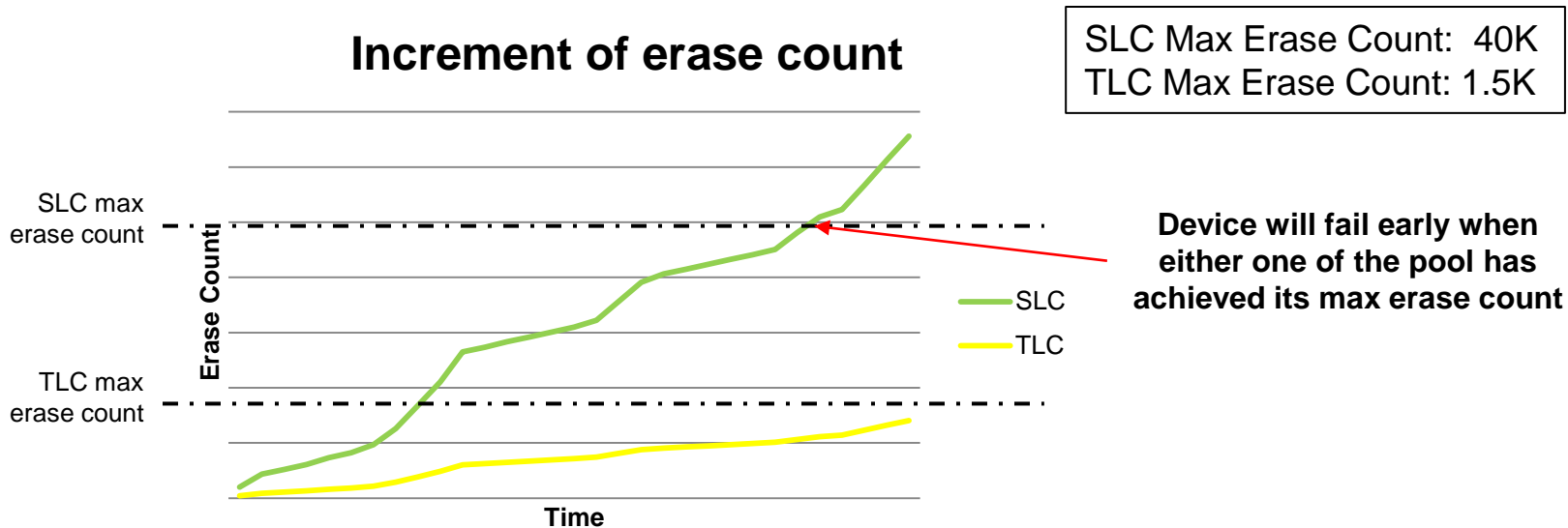
- Simulation results based on host usage model
- Saved 45% of NAND flash program during idle time

Mixed Pool Dynamic Wear Leveling



- The number of SLC/TLC blocks are usually allocated during device initialization
- We expect both SLC/TLC pools to wear out equally during device end of life

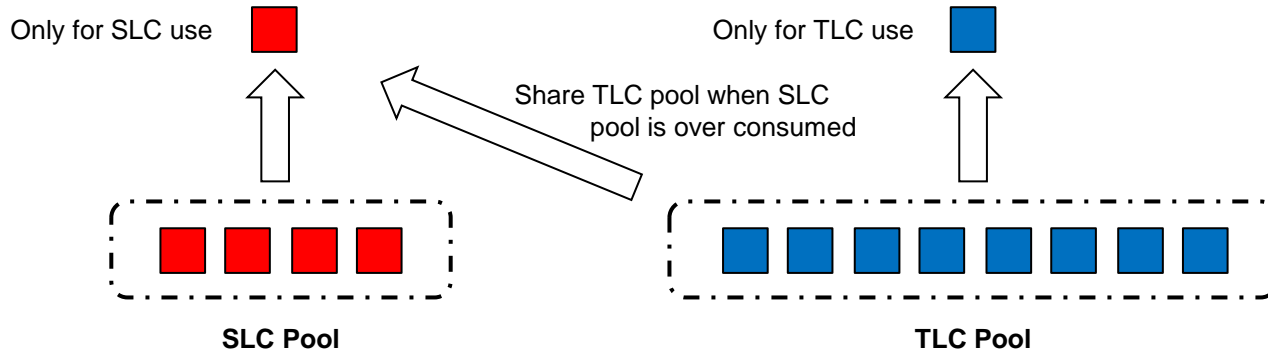
Mixed Pool Dynamic Wear Leveling



- However, different host I/O behavior might have different impact on SLC/TLC block usage



Mixed Pool Dynamic Wear Leveling

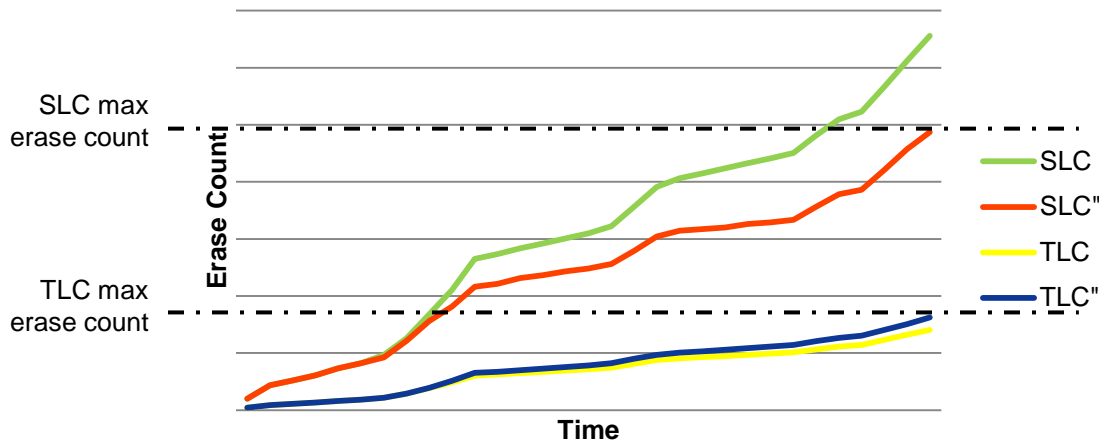


- Controller can constantly monitor the erase count ratio of both pools and dynamically configure the block selection algorithm to keep within reasonable TLC/SLC ratio

Mixed Pool Dynamic Wear Leveling

Increment of erase count

SLC Max Erase Count: 40K
TLC Max Erase Count: 1.5K



Lifetime extended
by 10%

- Simulation results based on host usage model
- This will prevent device to fail early due to wear out



Conclusion

- By exploring the key parameters of host behavior, system data structures, and NAND flash condition, a self learning FTL with simple adaptive design can benefit storage device in terms of performance, endurance, cost and flexibility



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THANK YOU